

International

IOR Rectifier

HEXFET® POWER MOSFET

JANTX2N6790

JANTXV2N6790

[REF:MIL-PRF-19500/555]

[GENERIC:IRFF220]

N-CHANNEL

200 Volt, 0.80Ω HEXFET

HEXFET technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry achieves very low on-state resistance combined with high transconductance.

HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits, and virtually any application where high reliability is required.

Product Summary

Part Number	BV _{DSS}	R _{DS(on)}	I _D
JANTX2N6790	200V	0.80Ω	3.5A
JANTXV2N6790			

Features:

- Avalanche Energy Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed

Absolute Maximum Ratings

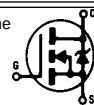
	Parameter	JANTX2N6790, JANTXV2N6790	Units
I _D @ V _{GS} = 10V, T _C = 25°C	Continuous Drain Current	3.5	A
I _D @ V _{GS} = 10V, T _C = 100°C	Continuous Drain Current	2.25	
I _{DM}	Pulsed Drain Current ①	14	
P _D @ T _C = 25°C	Max. Power Dissipation	20	W
	Linear Derating Factor	0.16	W/K ⑤
V _{GS}	Gate-to-Source Voltage	±20	V
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10.5 seconds)	
	Weight	0.98 (typical)	g

JANTX2N6790, JANTXV2N6790 Device

Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (Unless Otherwise Specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 1.0\text{ mA}$
$\Delta BV_{DSS}/\Delta T_j$	Temperature Coefficient of Breakdown Voltage	—	0.25	—	$V/^\circ\text{C}$	Reference to 25°C , $I_D = 1.0\text{ mA}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.80	Ω	$V_{GS} = 10V, I_D = 2.25A$ ④
		—	—	0.92		$V_{GS} = 10V, I_D = 3.5A$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	1.5	—	—	S (④)	$V_{DS} > 15V, I_{DS} = 2.25A$ ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	$V_{DS} = 0.8 \times \text{Max Rating}, V_{GS} = 0V$
		—	—	250		$V_{DS} = 0.8 \times \text{Max Rating}$ $V_{GS} = 0V, T_j = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20V$
I_{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	8.0	—	14.3	nC	$V_{GS} = 10V, I_D = 3.5A$ $V_{DS} = \text{Max. Rating} \times 0.5$ see figures 6 and 13
Q_{gs}	Gate-to-Source Charge	0.9	—	3.0		
Q_{gd}	Gate-to-Drain ("Miller") Charge	2.3	—	9.0		
$t_{d(on)}$	Turn-On Delay Time	—	—	40	ns	$V_{DD} = 100V, I_D = 3.5A,$ $R_G = 7.5\Omega, V_{GS} = 10V$ see figure 10
t_r	Rise Time	—	—	50		
$t_{d(off)}$	Turn-Off Delay Time	—	—	50		
t_f	Fall Time	—	—	50		
L_D	Internal Drain Inductance	—	5.0	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
L_S	Internal Source Inductance	—	15	—		Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.
C_{iss}	Input Capacitance	—	260	—	pF	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1.0\text{ MHz}$ see figure 5
C_{oss}	Output Capacitance	—	100	—		
C_{rss}	Reverse Transfer Capacitance	—	30	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	3.5	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier. 
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	14		
V _{SD}	Diode Forward Voltage	—	—	1.5	V	T _j = 25°C, I _S = 3.5A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	400	ns	T _j = 25°C, I _F = 3.5A, di/dt ≤ 100A/μs V _{DD} ≤ 50V ④
Q _{RR}	Reverse Recovery Charge	—	—	4.3	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
R_{thJC}	Junction-to-Case	—	—	6.25	K/W	
R_{thJA}	Junction-to-Ambient	—	—	175		Typical socket mount

JANTX2N6790, JANTXV2N6790 Device

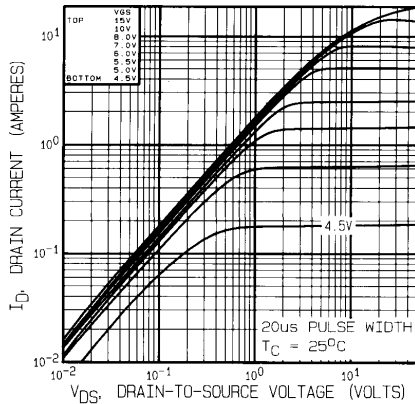


Fig. 1 — Typical Output Characteristics
 $T_C = 25^\circ\text{C}$

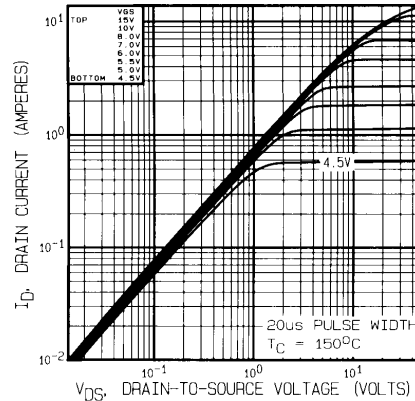


Fig. 2 — Typical Output Characteristics
 $T_C = 150^\circ\text{C}$

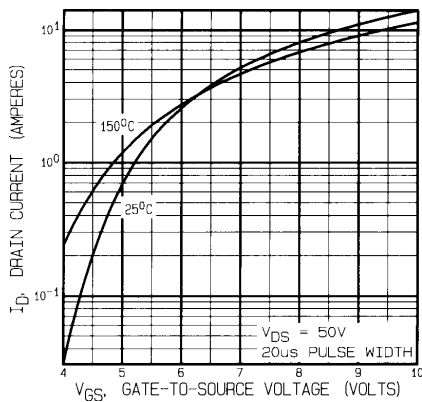


Fig. 3 — Typical Transfer Characteristics

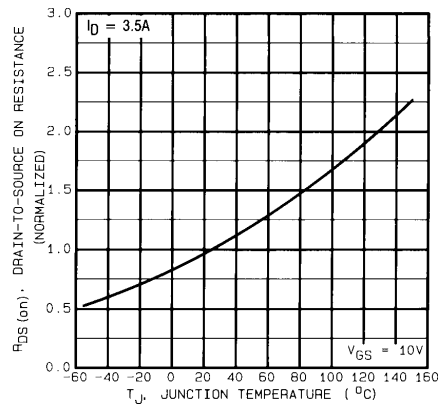


Fig. 4 — Normalized On-Resistance Vs. Temperature

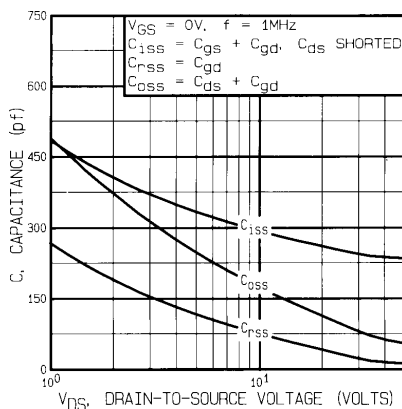


Fig. 5 — Typical Capacitance Vs. Drain-to-Source Voltage

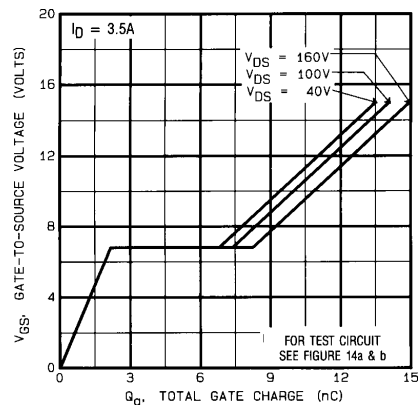


Fig. 6 — Typical Gate Charge Vs. Gate-to-Source Voltage

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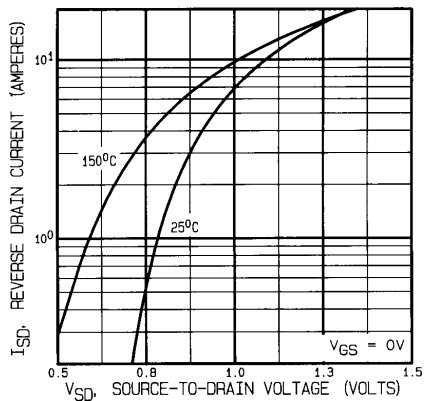


Fig. 7 — Typical Source-to-Drain Diode Forward Voltage

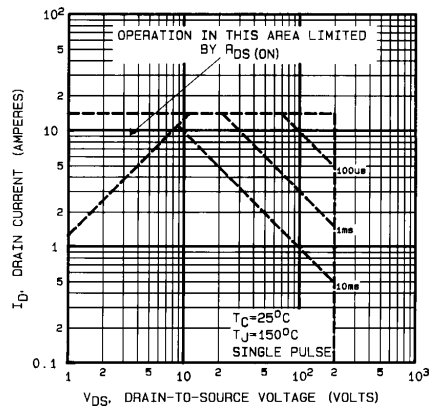


Fig. 8 — Maximum Safe Operating Area

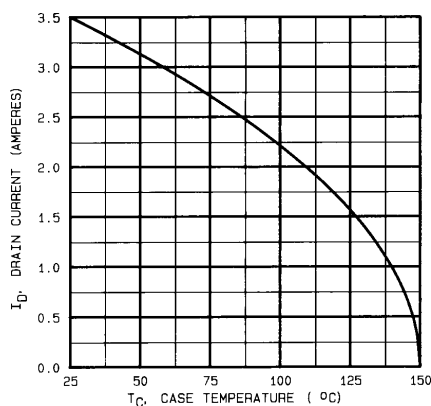


Fig. 9 — Maximum Drain Current Vs. Case Temperature

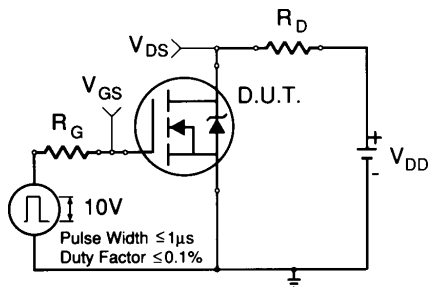


Fig. 10a — Switching Time Test Circuit

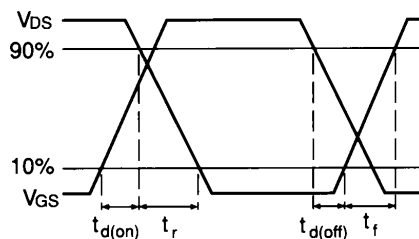


Fig. 10b — Switching Time Waveforms

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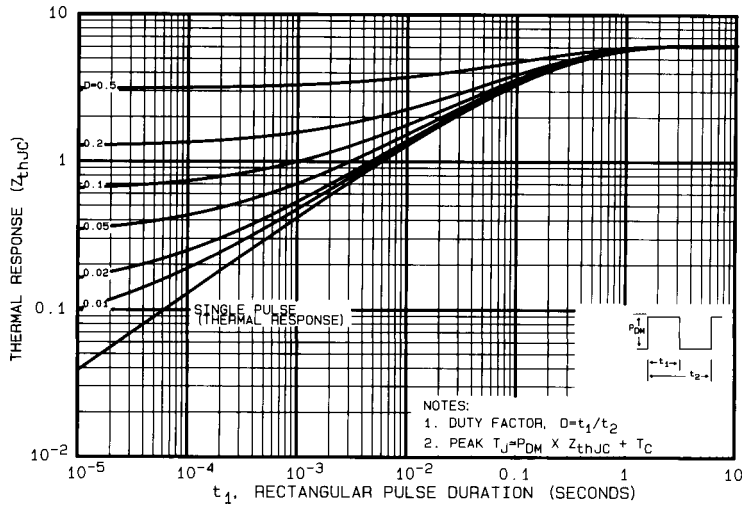


Fig. 11 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

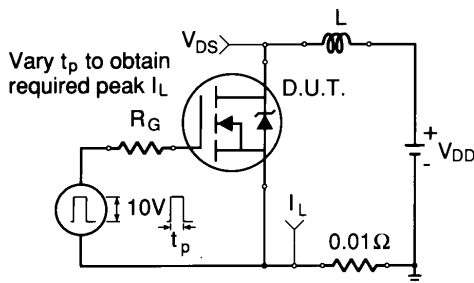


Fig. 12a — Unclamped Inductive Test Circuit

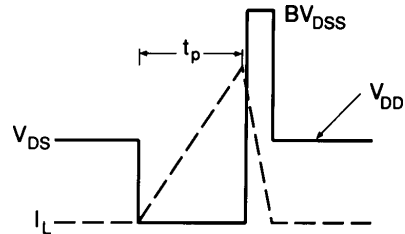


Fig. 12b — Unclamped Inductive Waveforms

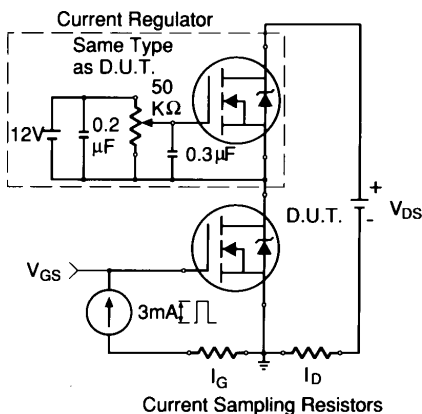


Fig. 13a — Gate Charge Test Circuit

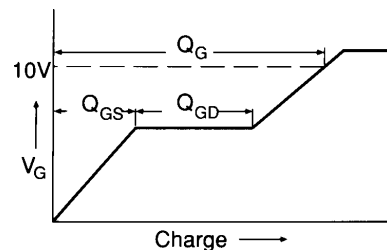


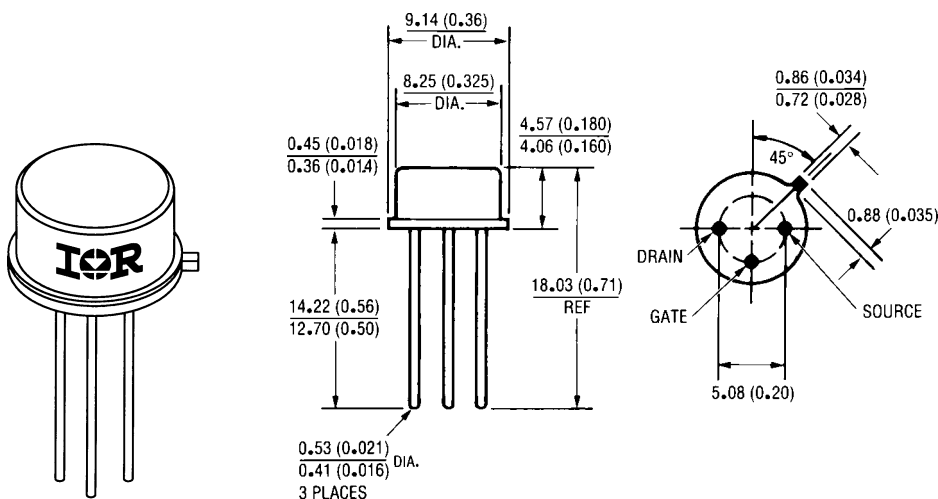
Fig. 13b — Basic Gate Charge Waveform

JANTX2N6790, JANTXV2N6790 Device



- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
(see figure 11)
- ② @ $V_{DD} = 50V$, Starting $T_J = 25^\circ C$,
 $EAS = [0.5 * L * (I_L^2) * [BV_{DSS}/(BV_{DSS} - V_{DD})]]$
 Peak $I_L = 3.5A$, $V_{GS} = 10V$, $25 \leq R_G \leq 200\Omega$
- ③ $I_{SD} \leq 3.5A$, $di/dt \leq 95A/\mu s$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ $K/W = ^\circ C/W$
 $W/K = W/^\circ C$

Case Outline and Dimensions — TO-205AF (Modified TO-39)



All dimensions are shown millimeters (inches)

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WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 3-30-4 Nishi-Ikeburo 3-Chome, Toshima-Ki, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

<http://www.irf.com/>

Data and specifications subject to change without notice.

10/96

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